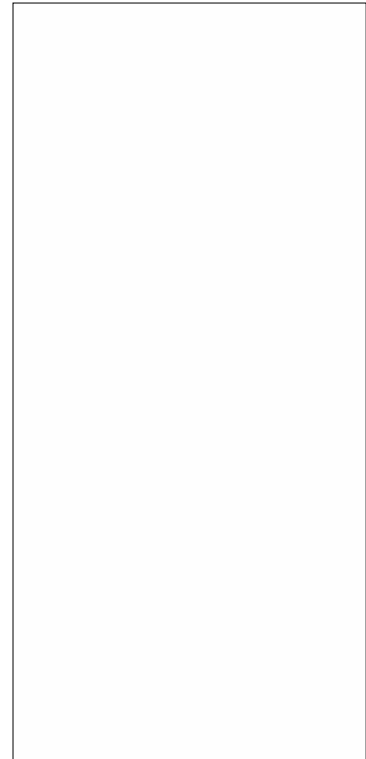




JCT612FH 12A SCR

Rev.A.1.1

With high ability to withstand





Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	0.2	-	-	V

 I_{LV}

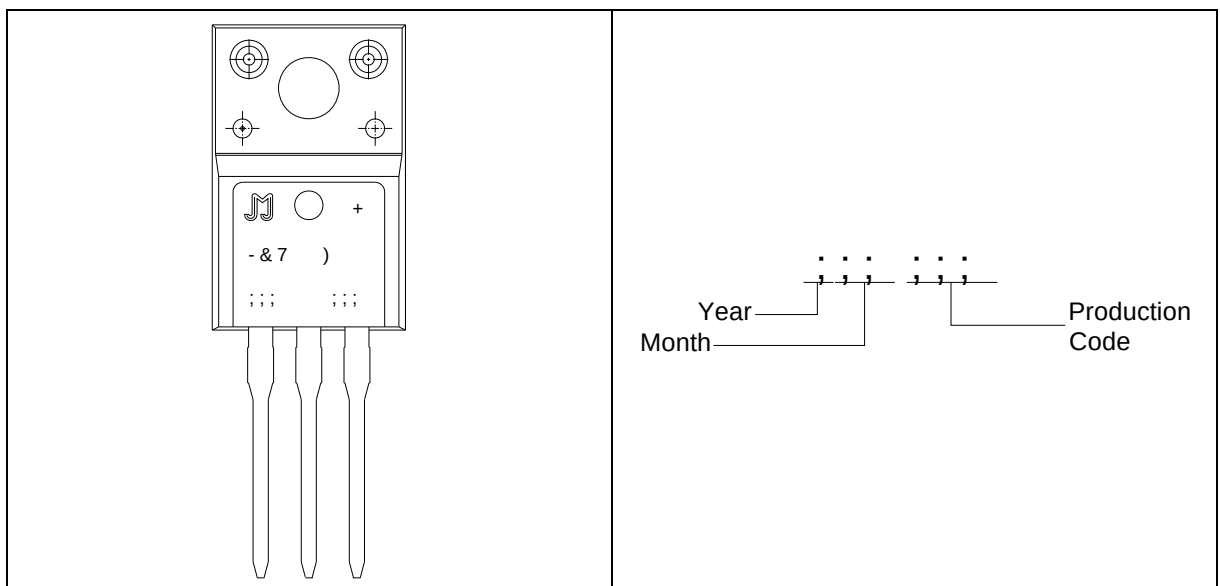
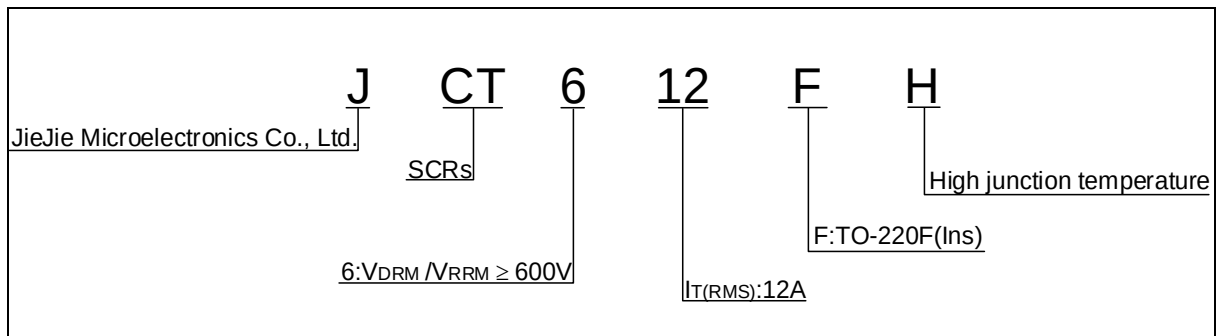


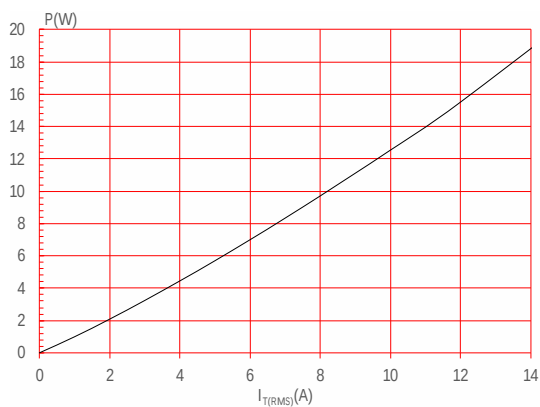
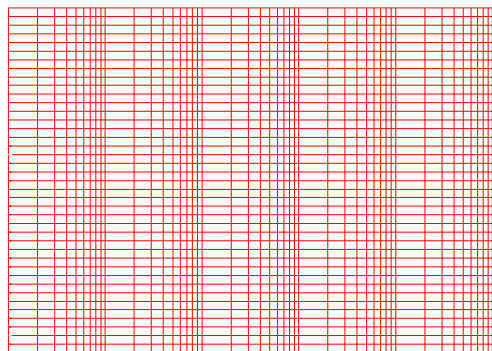
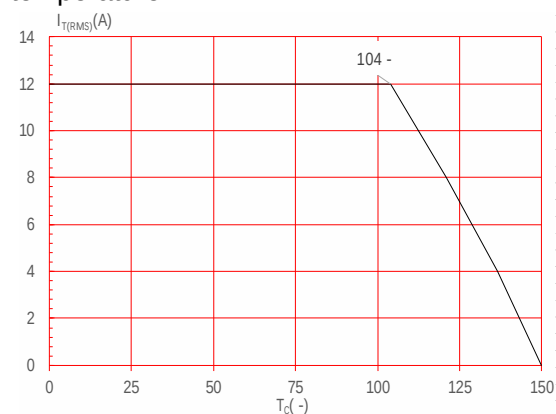
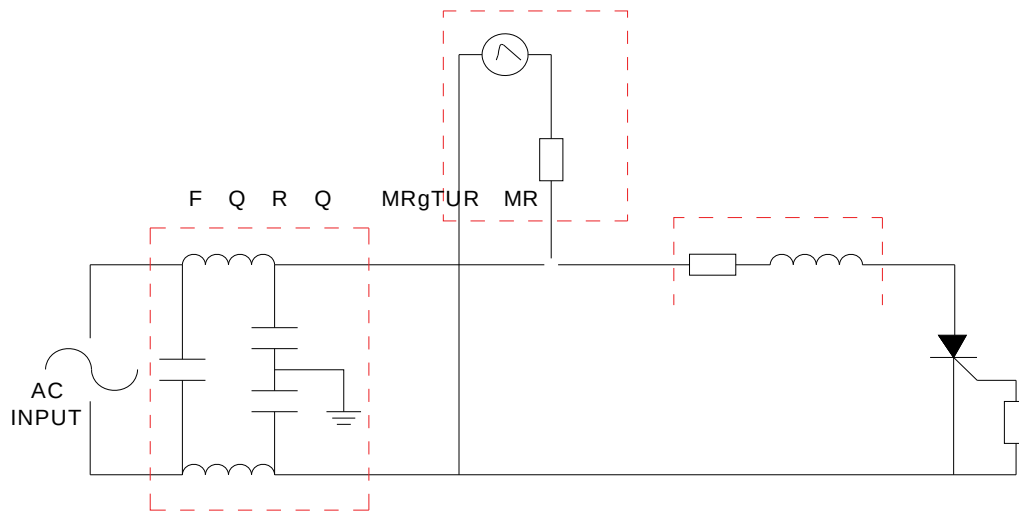
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.3:** Surge peak on-state current versus number of cycles**FIG.2:** RMS on-state current versus case temperature**FIG.4:** On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT612FH	600	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Jun.12, 2023	A.1.0	Last update
Oct.17, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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